# **Noninverting 3-State Buffer**

The MC74VHC1G126 is an advanced high speed CMOS noninverting 3-state buffer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including a buffered 3–state output which provides high noise immunity and stable output.

The MC74VHC1G126 input structure provides protection when voltages up to 7 V are applied, regardless of the supply voltage. This allows the MC74VHC1G126 to be used to interface 5 V circuits to 3 V circuits.

#### **Features**

- High Speed:  $t_{PD} = 3.5 \text{ ns}$  (Typ) at  $V_{CC} = 5 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 1 \mu A \text{ (Max)}$  at  $T_A = 25^{\circ}\text{C}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Pin and Function Compatible with Other Standard Logic Families
- Chip Complexity: FETs = 58; Equivalent Gates = 15
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

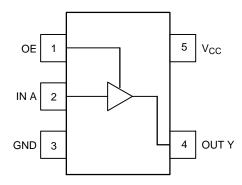


Figure 1. Pinout (Top View)



Figure 2. Logic Symbol



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MARKING DIAGRAMS



SC-88A / SOT-353 / SC-70 DF SUFFIX CASE 419A





TSOP-5 / SOT-23 / SC-59 DT SUFFIX CASE 483



W2 = Device Code
M = Date Code\*
= Pb-Free Package

(Note: Microdot may be in either location)
\*Date Code orientation and/or position may vary depending upon manufacturing location.

PIN ASSIGNMENT				
1	OE			
2	IN A			
3	GND			
4	OUT Y			
5	V <sub>CC</sub>			

#### **FUNCTION TABLE**

A Input	OE Input	Y Output
L	Н	L
Н	Н	Н
X	L	Z

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

#### **MAXIMUM RATINGS**

Symbol	Characteristics	Value	Unit
V <sub>CC</sub>	DC Supply Voltage	-0.5 to +7.0	V
V <sub>IN</sub>	DC Input Voltage	-0.5 to +7.0	V
V <sub>OUT</sub>	DC Output Voltage $V_{CC} = High \text{ or Low Stat}$		V
I <sub>IK</sub>	Input Diode Current	-20	mA
I <sub>OK</sub>	Output Diode Current $V_{OUT} < GND; V_{OUT} > V_{C}$	+20	mA
I <sub>OUT</sub>	DC Output Current, per Pin	+25	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND	+50	mA
$P_{D}$	Power dissipation in still air SC–88A, TSOP–	5 200	mW
$\theta_{JA}$	Thermal resistance SC-88A, TSOP-	333	°C/W
TL	Lead temperature, 1 mm from case for 10 secs	260	°C
TJ	Junction temperature under bias	+150	°C
T <sub>stg</sub>	Storage temperature	-65 to +150	°C
V <sub>ESD</sub>	ESD Withstand Voltage  Human Body Model (Note 1  Machine Model (Note 2  Charged Device Model (Note 3	> 200	V
I <sub>Latchup</sub>	Latchup Performance Above V <sub>CC</sub> and Below GND at 125°C (Note 4	) ±500	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- Tested to EIA/JESD22-A114-A
   Tested to EIA/JESD22-A115-A
- 3. Tested to JESD22-C101-A
- 4. Tested to EIA/JESD78

#### RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage	2.0	5.5	V
V <sub>IN</sub>	DC Input Voltage	0.0	5.5	V
V <sub>OUT</sub>	DC Output Voltage	0.0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature Range	-55	+125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time $ V_{CC} = 3.3 \text{ V} \pm 0. \\ V_{CC} = 5.0 \text{ V} \pm 0. $	3 V 0 5 V 0	100 20	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

#### **Device Junction Temperature versus** Time to 0.1% Bond Failures

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

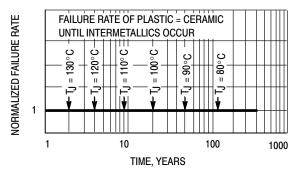


Figure 3. Failure Rate vs. Time Junction Temperature

#### DC ELECTRICAL CHARACTERISTICS

			v <sub>cc</sub>	Т	A = 25°	С	T <sub>A</sub> ≤	85°C	-55 ≤ T <sub>A</sub>	≤ 125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage		2.0 3.0 4.5 5.5	1.5 2.1 3.15 3.85			1.5 2.1 3.15 3.85		1.5 2.1 3.15 3.85		V
V <sub>IL</sub>	Maximum Low-Level Input Voltage		2.0 3.0 4.5 5.5			0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65	V
V <sub>OH</sub>	Minimum High–Level Output Voltage V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu A$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		V
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -4 \text{ mA}$ $I_{OH} = -8 \text{ mA}$	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		V
V <sub>OL</sub>	Maximum Low–Level Output Voltage V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50  \mu\text{A}$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 4 \text{ mA}$ $I_{OL} = 8 \text{ mA}$	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	V
I <sub>OZ</sub>	Maximum 3–State Leakage Current	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = V_{CC} \text{ or GND}$	5.5			±0.2 5		±2.5		±2.5	μΑ
I <sub>IN</sub>	Maximum Input Leakage Current	V <sub>IN</sub> = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±1.0	μΑ
I <sub>CC</sub>	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			1.0		20		40	μΑ

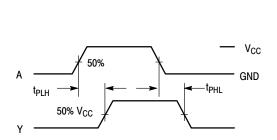
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

#### AC ELECTRICAL CHARACTERISTICS $C_{load} = 50$ pF, Input $t_r = t_f = 3.0$ ns

				Т	A = 25°	С	T <sub>A</sub> ≤	85°C	-55 ≤ T <sub>A</sub>	≤ 125°C	
Symbol	Parameter	Test Condit	tions	Min	Тур	Max	Min	Max	Min	Max	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Input A to Y	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	$C_L = 15 pF$ $C_L = 50 pF$		4.5 6.4	8.0 11.5		9.5 13.0		12.0 16.0	ns
	(Figures 3. and 5.)	$V_{CC} = 5.0 \pm 0.5 \text{ V}$	$C_L = 15 pF$ $C_L = 50 pF$		3.5 4.5	5.5 7.5		6.5 8.5		8.5 10.5	
t <sub>PZL</sub> , t <sub>PZH</sub>	Maximum Output Enable Time, Input OE to Y	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $R_L = 1000 \Omega$			4.5 6.4	8.0 11.5		9.5 13.0		11.5 15.0	ns
	(Figures 4. and 5.)	$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $R_L = 1000 \Omega$			3.5 4.5	5.1 7.1		6.0 8.0		8.5 10.5	
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Maximum Output Disable Time, Input OE to Y	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $R_L = 1000 \Omega$	$C_L = 15 pF$ $C_L = 50 pF$		6.5 8.0	9.7 13.2		11.5 15.0		14.5 18.0	ns
	(Figures 4. and 5.)	$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $R_L = 1000 \Omega$	$C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		4.8 7.0	6.8 8.8		8.0 10.0		10.0 12.0	
C <sub>IN</sub>	Maximum Input Capacitance				4.0	10		10		10	pF
C <sub>OUT</sub>	Maximum 3-State Output Capacitance (Output in High Impedance State)				6.0						pF
			Typical @ 25°C, V <sub>CC</sub> = 5.0 V								
C <sub>PD</sub>	Power Dissipation Capacit	ance (Note 5)					8.0	)			pF

<sup>5.</sup> C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>. C<sub>PD</sub> is used to determine the no–load dynamic power consumption; P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.

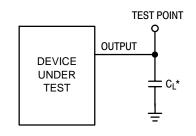
#### **SWITCHING WAVEFORMS**

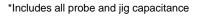


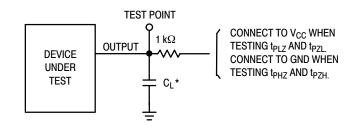
 $V_{\text{CC}}$ 0E 50% GND  $t_{PZL}$  $t_{PLZ}$ HIGH **IMPEDANCE** 50% V<sub>CC</sub>  $V_{OL} + 0.3V$  $t_{\text{PHZ}}$  $t_{PZH}$ V<sub>OH</sub> - 0.3V 50% V<sub>CC</sub> HIGH IMPEDANCE

Figure 4. Switching Waveforms

Figure 5.







\*Includes all probe and jig capacitance

Figure 6. Test Circuit

Figure 7. Test Circuit

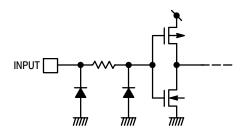


Figure 8. Input Equivalent Circuit

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
M74VHC1G126DFT1G		
NLVVHC1G126DFT1G*	SC-88A/SOT-353/SC-70	
M74VHC1G126DFT2G	(Pb-Free)	3000 Units / Tape & Reel
NLVVHC1G126DFT2G*		·
M74VHC1G126DTT1G	TSOP-5/SOT-23/SC-59 (Pb-Free)	

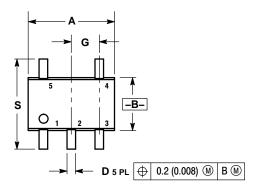
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

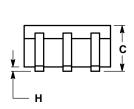
<sup>\*</sup>NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable

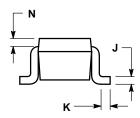
#### **PACKAGE DIMENSIONS**

# SC-88A (SC-70-5/SOT-353) CASE 419A-02

ISSUE L



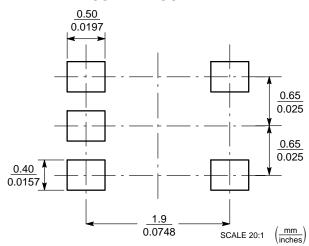




- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. 419A-01 OBSOLETE. NEW STANDARD 419A-02.
  4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

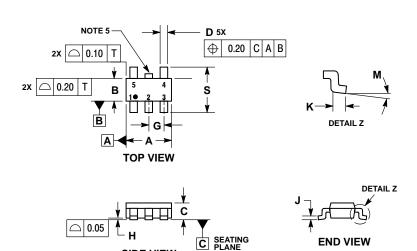
	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.071	0.087	1.80	2.20
В	0.045	0.053	1.15	1.35
С	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026	BSC	0.65	BSC
Н		0.004		0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008	REF	0.20	REF
S	0.079	0.087	2 00	2 20

#### **SOLDER FOOTPRINT**



#### PACKAGE DIMENSIONS

#### TSOP-5 CASE 483 ISSUE M



**SIDE VIEW** 

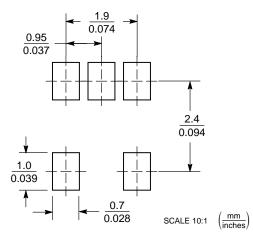
#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL
- MINIMUM THICKNESS OF BASE MATERIAL.

  4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSION A.
- 5. OPTIONAL CONSTRUCTION: AN ADDITIONAL TRIMMED LEAD IS ALLOWED IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY.

	MILLIMETERS						
DIM	MIN	MAX					
Α	2.85	3.15					
В	1.35	1.65					
С	0.90	1.10					
D	0.25	0.50					
G	0.95	0.95 BSC					
Н	0.01	0.10					
J	0.10	0.26					
K	0.20	0.60					
M	0°	10°					
S	2.50	3.00					

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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